

SEMICONDUCTOR TECHNICAL DATA

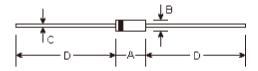
1N5817 ~ 1N5819

Schottky Barrier Rectifier Reverse Voltage 20V~40V, Forward Current 1.0 Ampere

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction, majority carrier conduction
- Guardring for overvoltage protection
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- High temperature soldering guaranteed: 250°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3Kg) tension

DO-41



DIMENSIONS										
DIM	inches		mm		Note					
	Min.	Max.	Min.	Max.	Note					
Α	0.165	0.205	4.2	5.2						
В	0.079	0.106	2.0	2.7	ф					
С	0.028	0.034	0.71	0.86	ф					
D	1.000	-	25.40	-						

Mechanical Data

• Case: DO-41 molded plastic body

 Terminals: Plated axial leads, solderable per MIL-STD-750. method 2026

• Polarity: Color band denotes cathode end

Mounting Position: AnyWeight: 0.012 ounce, 0.33 gram

Maximum Ratings and Electrical Characteristics

	Symbols	1N5817	1N5818	1N5819	Units
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	Volts
Maximum RMS voltage	V _{RMS}	14	21	28	Volts
Maximum DC blocking voltage	V _{DC}	20	30	40	Volts
Maximum non-repetitive peak reverse voltage	V _{RSM}	24	36	48	Volts
Maximum average forward rectified current 0.375" (9.5mm) lead length at T $_{\rm L}$ =90 $^{\circ}{\rm C}$	I _(AV)	1.0			Amp
Peak forward surge current, 8.3mS single half sine-wave superimposed on rated load (MIL-STD-750D 4066 method) at $\rm T_L$ =70 $\rm ^{\circ}C$	FSM	25.0			Amps
Maximum instantaneous forward voltage at 1.0A (Note 1) Maximum instantaneous forward voltage at 3.1A (Note 1)	V _F	0.450 0.750	0.550 0.875	0.600 0.900	Volts Volts
Maximum instantaneous reverse current T _A =25°C(Note1) at rated DC blocking voltage T _A =100°C	I _R		1.0 10.0		mA
Typical junction capacitance (Note 3)	C _J	110.0			ρF
Typical thermal resistance (Note 2)	R _{⊕JA} R _{⊕JL}		50.0 15.0		°C/W
Operating junction and storage temperature range	T _J , T _{STG}		-65 to +125		$^{\circ}$

Notes:

- (1) Pulse test: 300uS pulse width, 1% duty cycle
- (2) Thermal resistance from junction to lead, and/or to ambient P.C.B. mounted with 0.375" (9.5mm) lead length with 1.5X1.5" (38X38mm) copper pads
- (3) Measured at 1.0MHz and applied reverse voltage of 4.0 volts

Revision No: 0





RATINGS AND CHARACTERISTIC CURVES

